

UIN – 228001199

Section – 601

Lab Number – 1

Lab Report

MOS Device

Characterization

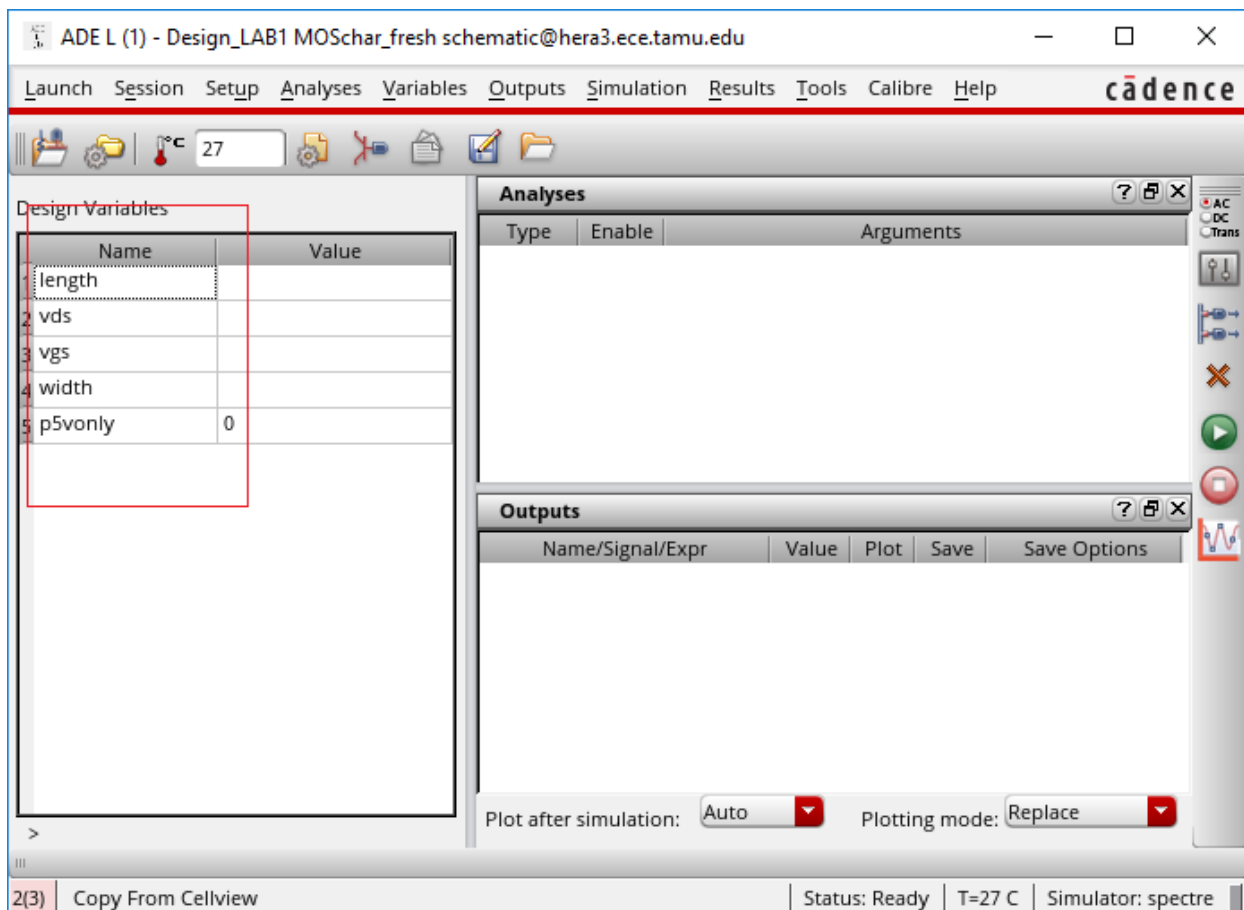
**Name – Bupathy Sudan
Rohit**

Description

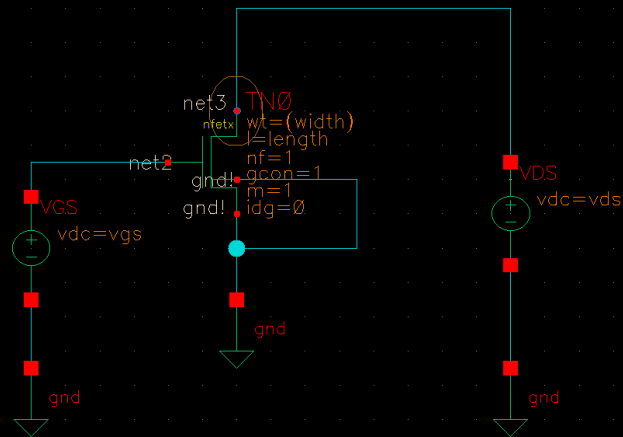
This lab exercise is about the MOS device characterization. The G_m/I_d technique is used to deduce the required information about the given MOS device. The parameters are estimated for different MOS devices with varying W/L ratios and the Device parameters are tabulated as reference for future circuit design.

Design

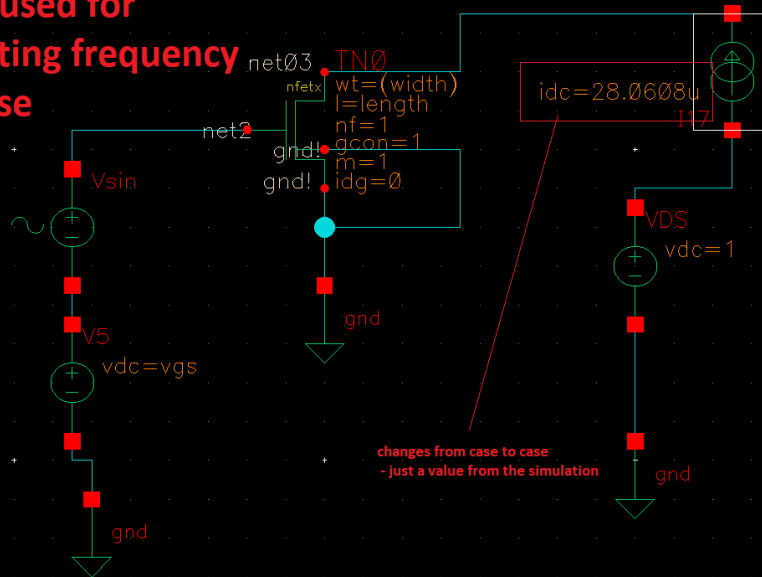
The following section includes all the circuit diagrams used for extracting the MOS device characteristics. As the same circuit is used for estimation of parameters over different W/L ratios, the generic circuit diagram for the NMOS and PMOS devices have been included. The W-width and L-Length has been turned into variables to increase reusability. Before running the simulation these values are set to their appropriate values based on the required sweeping.

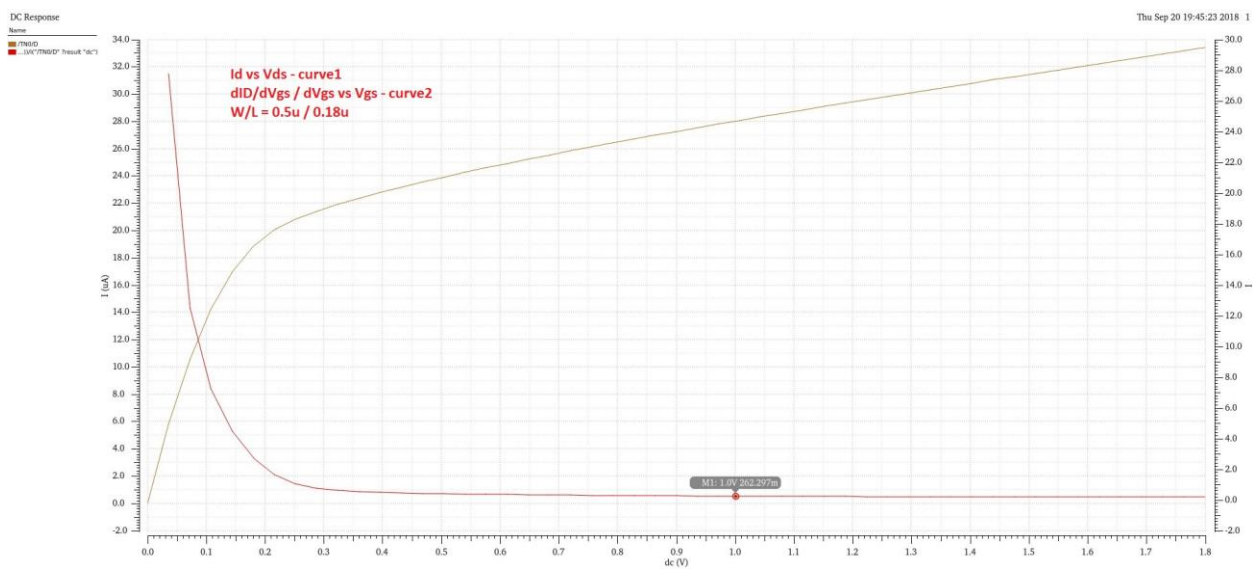
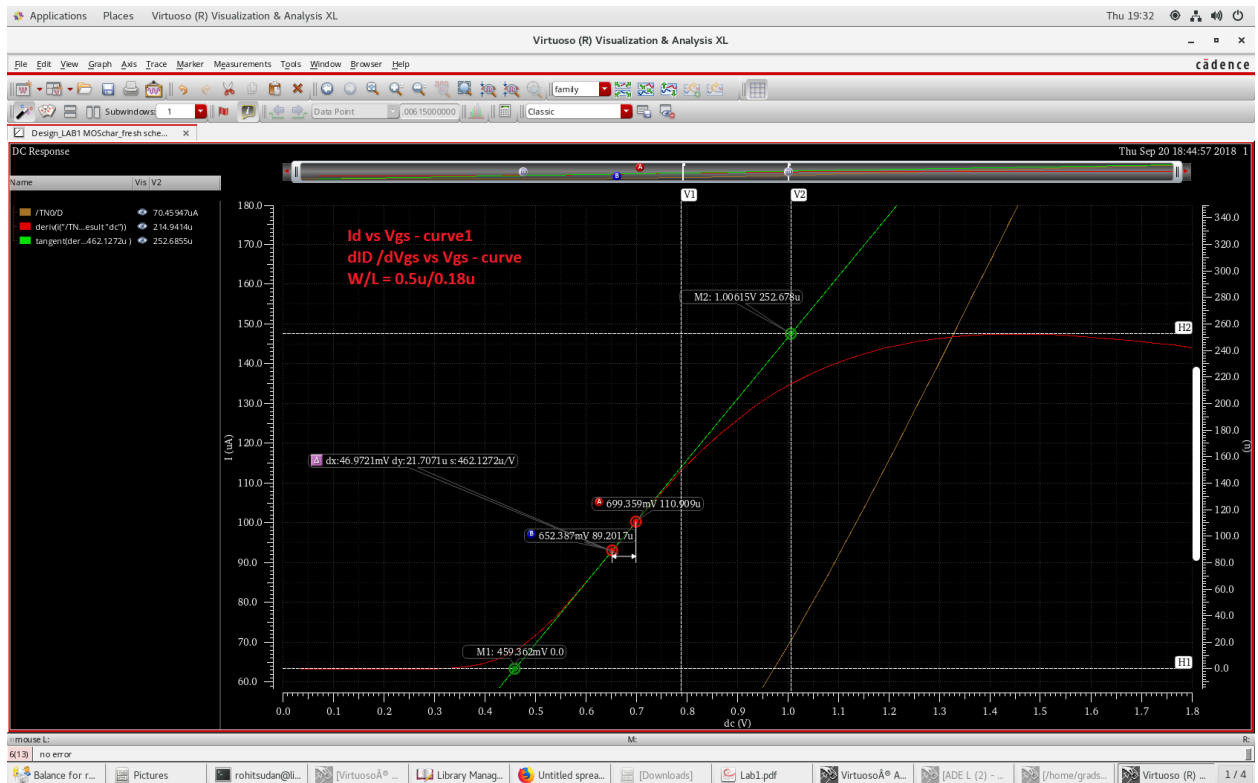


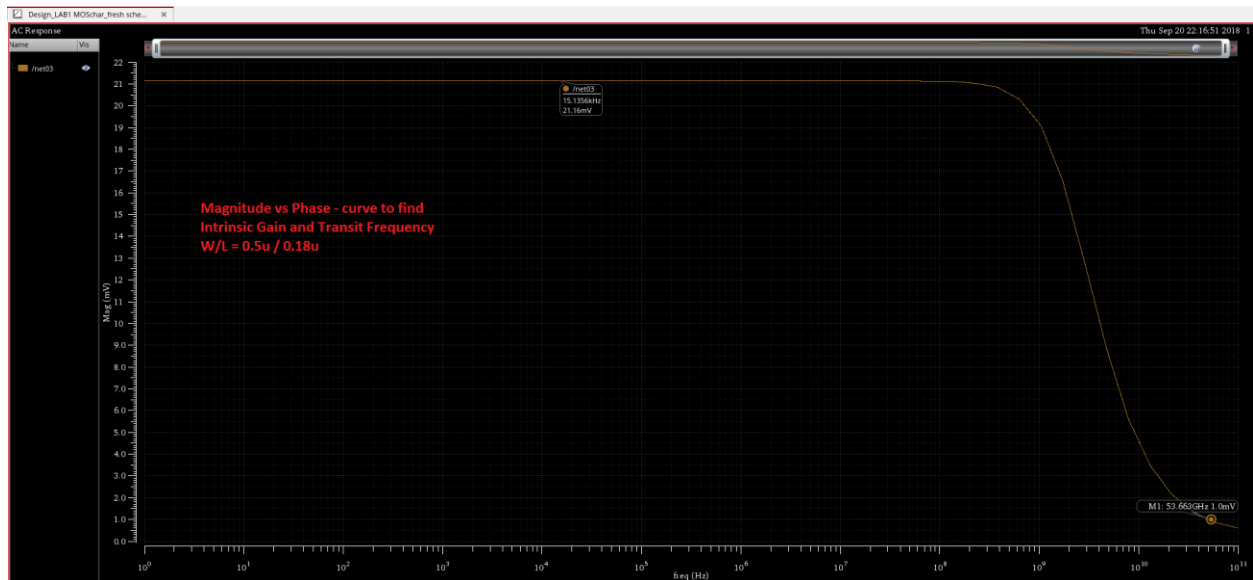
NMOS circuit used for V_{gs} vs I_d and V_{ds} vs I_d (For different Values of W/L)



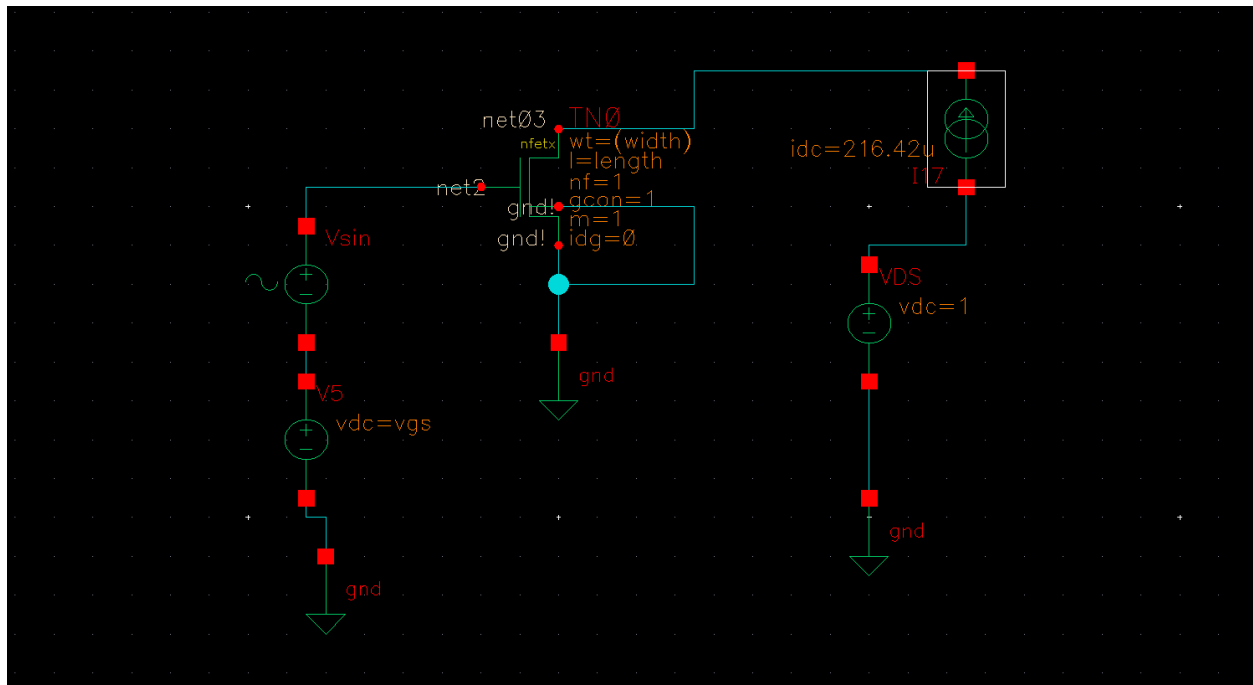
Circuit used for generating frequency response

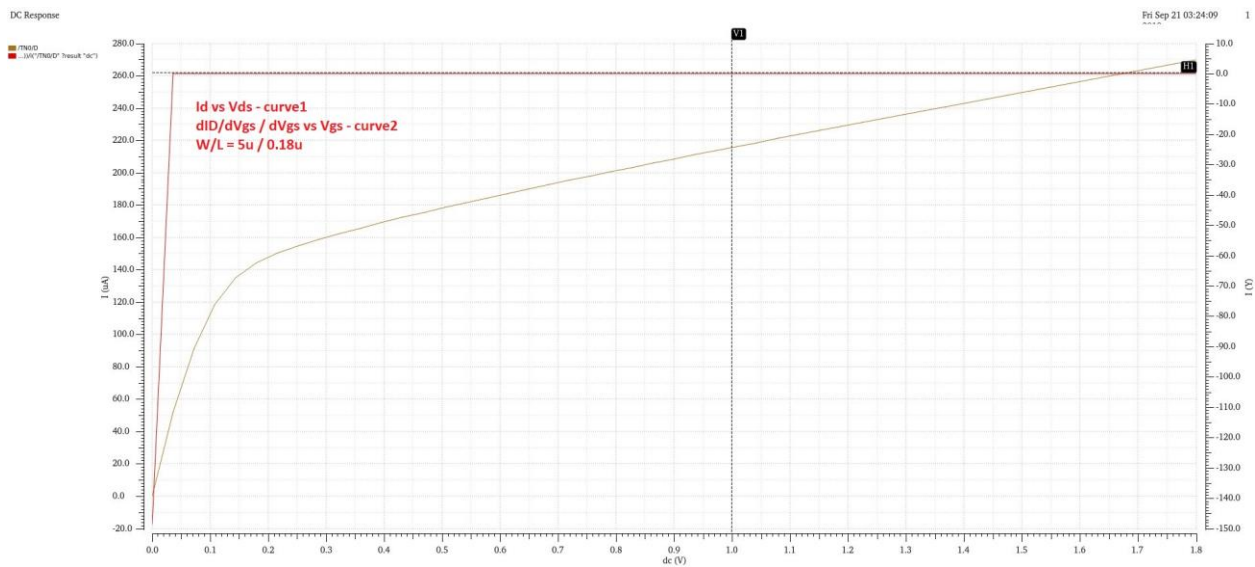
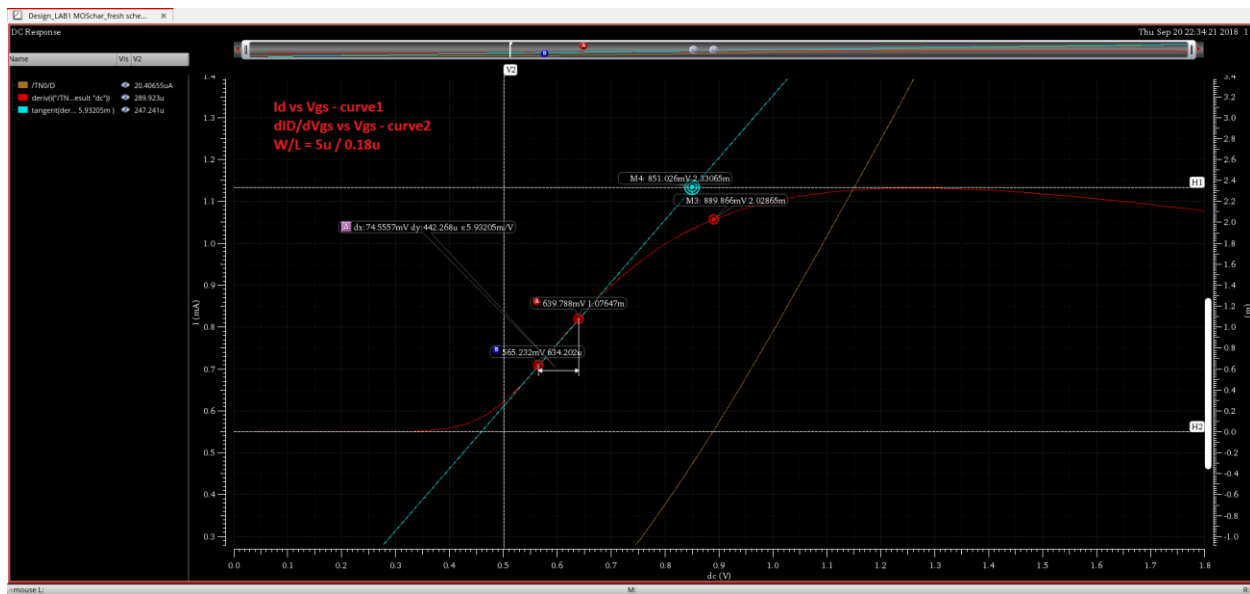


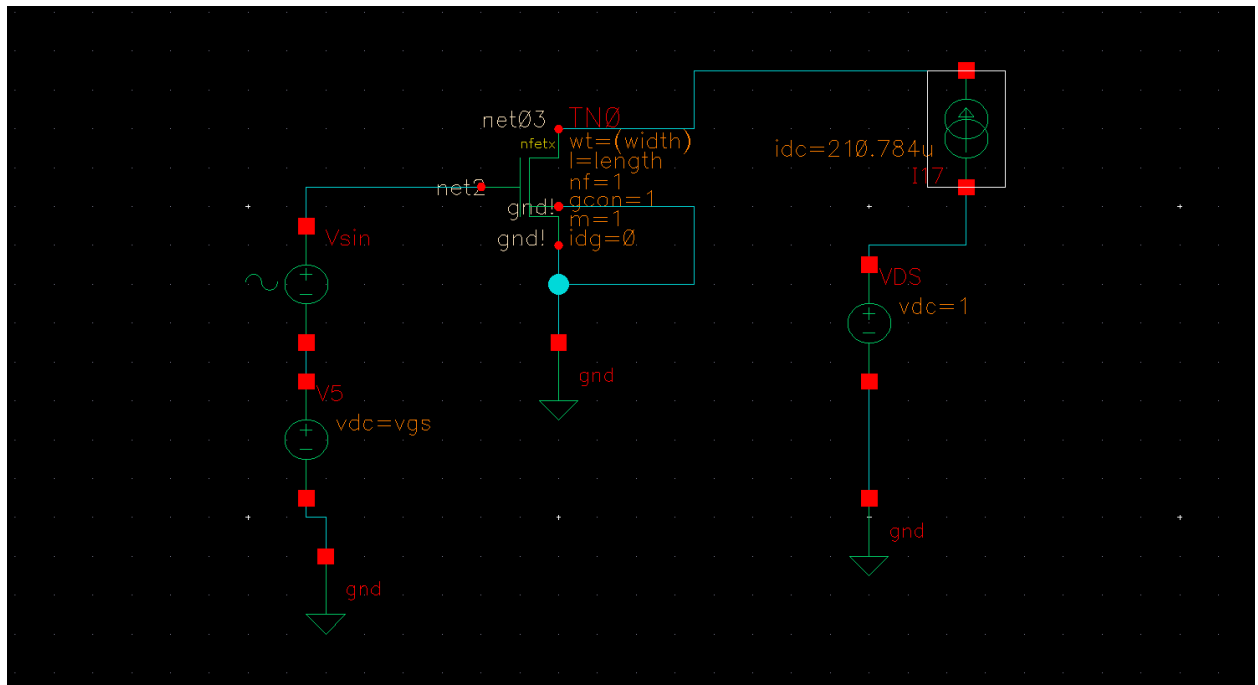
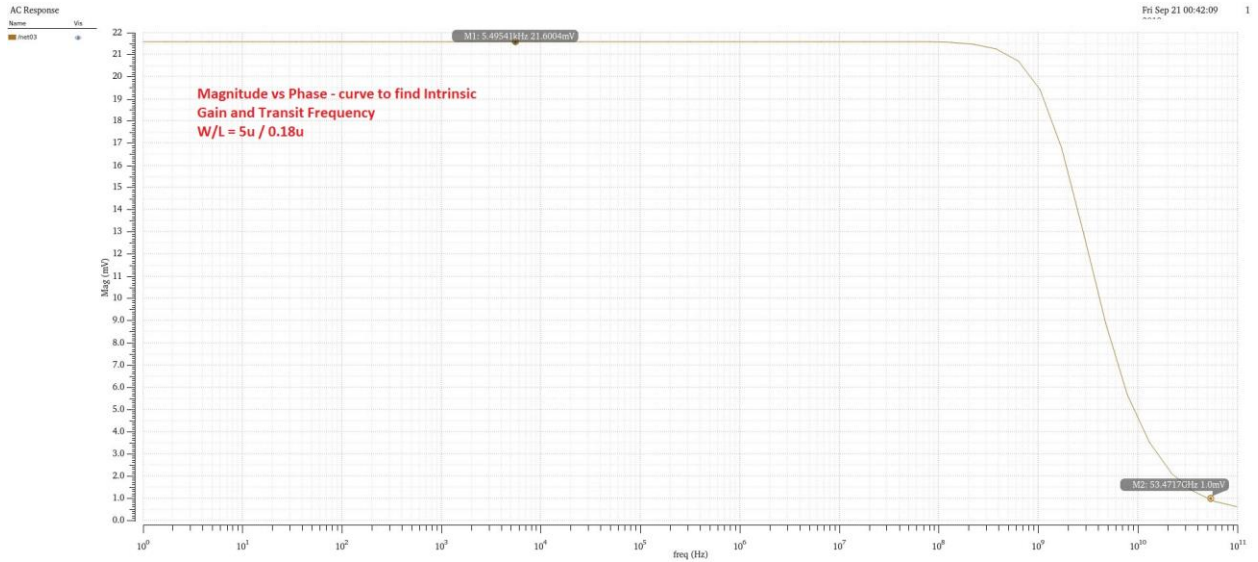




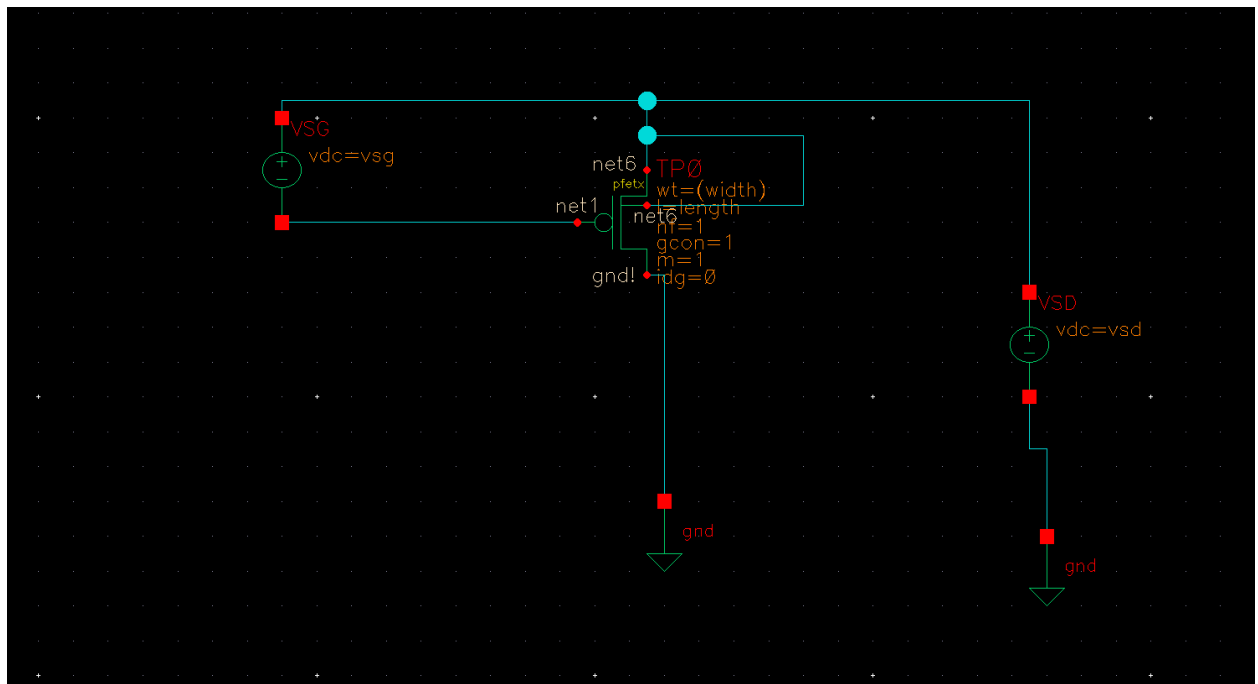
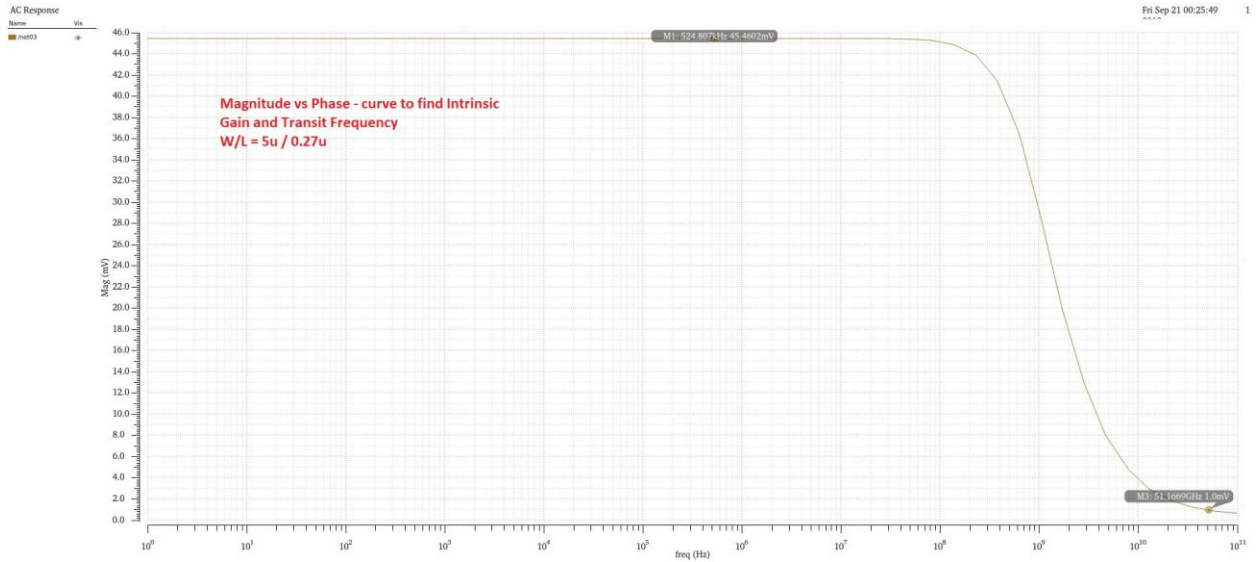
Circuit Used to Generate Frequency Response



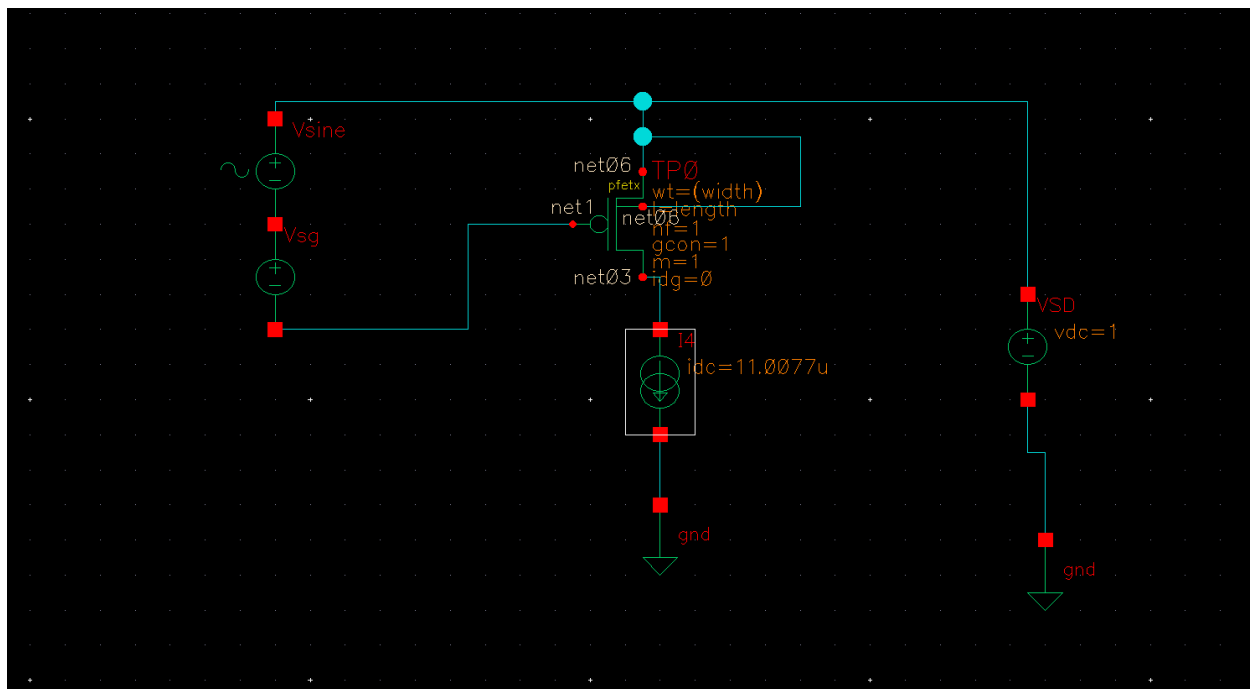




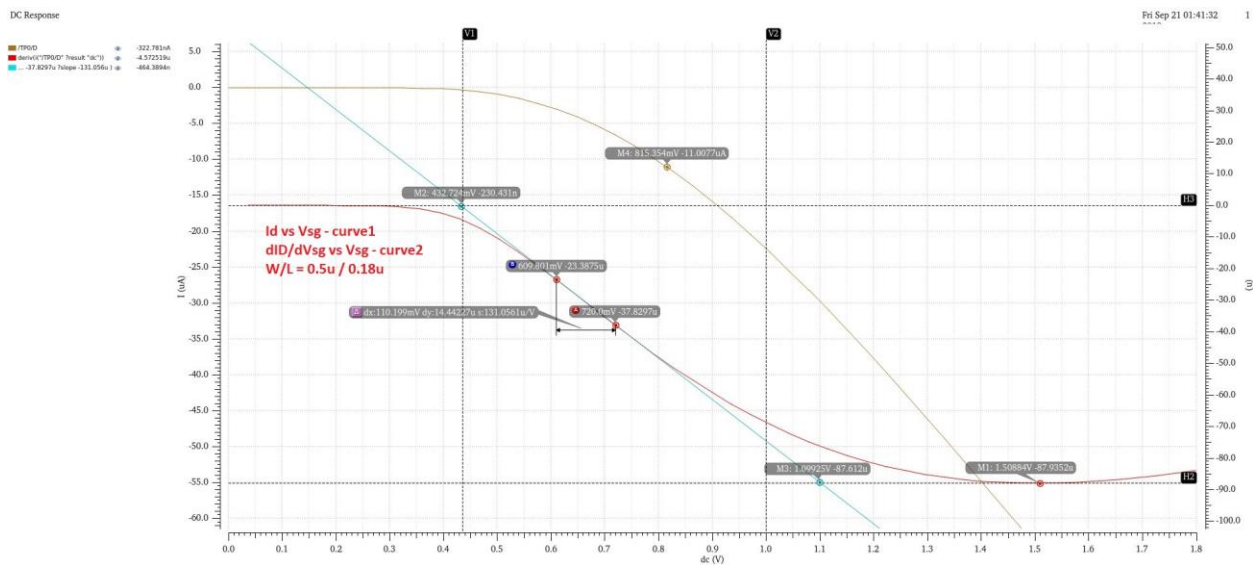
Circuit Used to Generate Frequency Response



PMOS circuit used for G_m/I_d parameter estimation



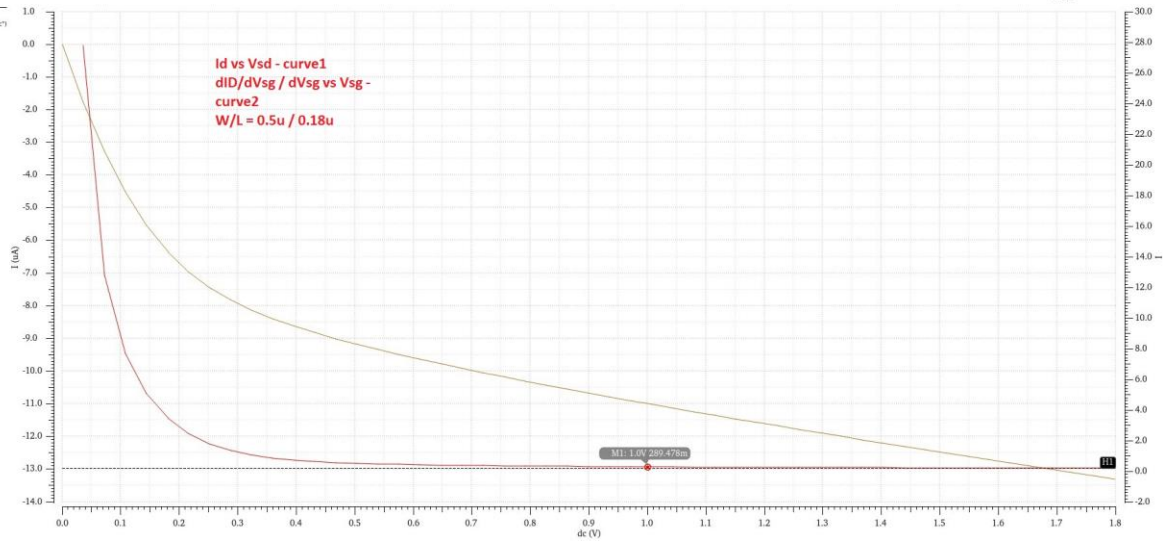
Circuit Used to Generate Frequency Response



DC Response

Fri Sep 21 01:54:31 1

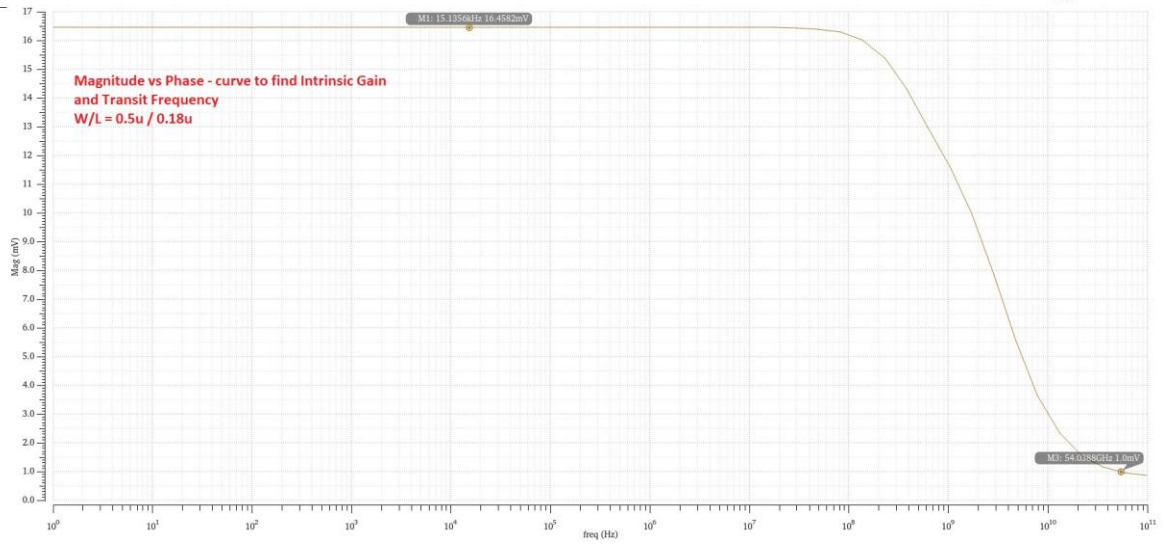
Name
■ plot0
■ (W/L)TRSD* Transluc ("a")

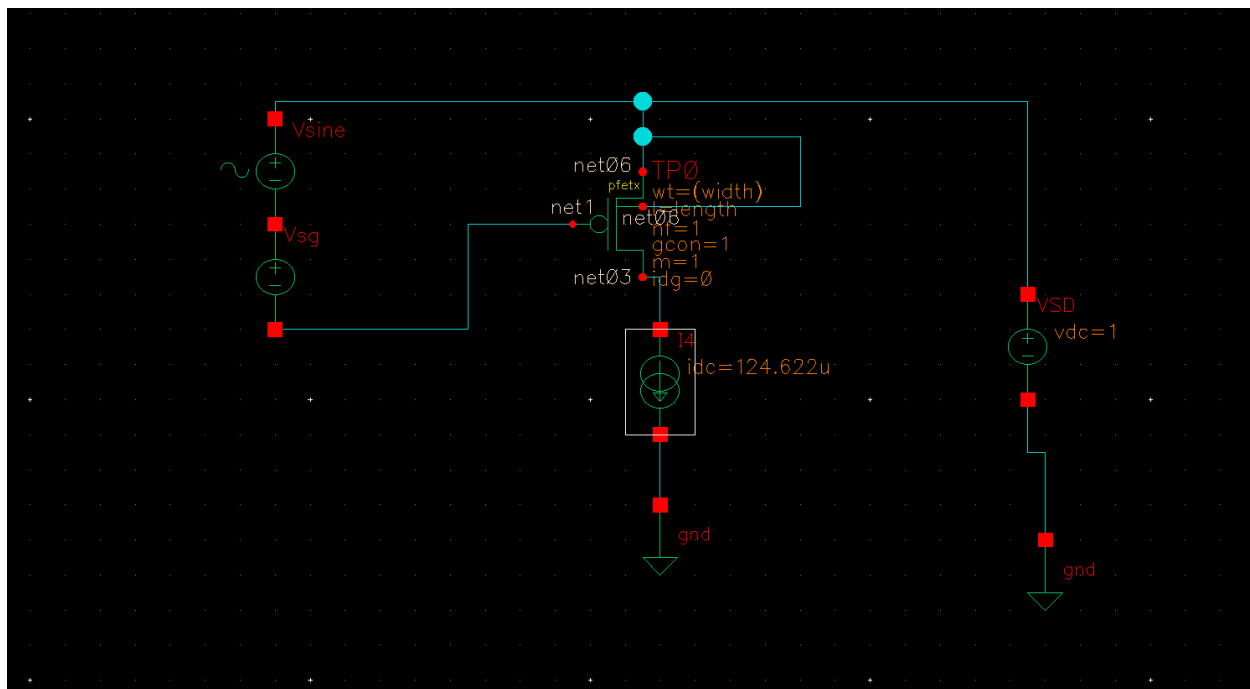


AC Response

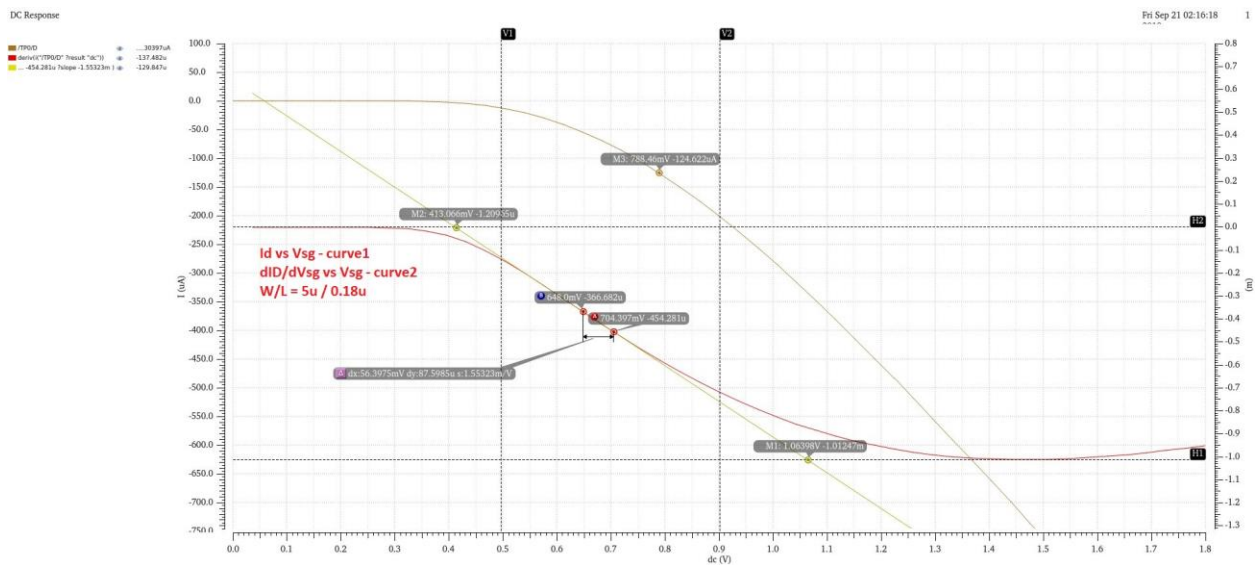
Fri Sep 21 02:11:27 1

Name
■ plot03
■ Vis



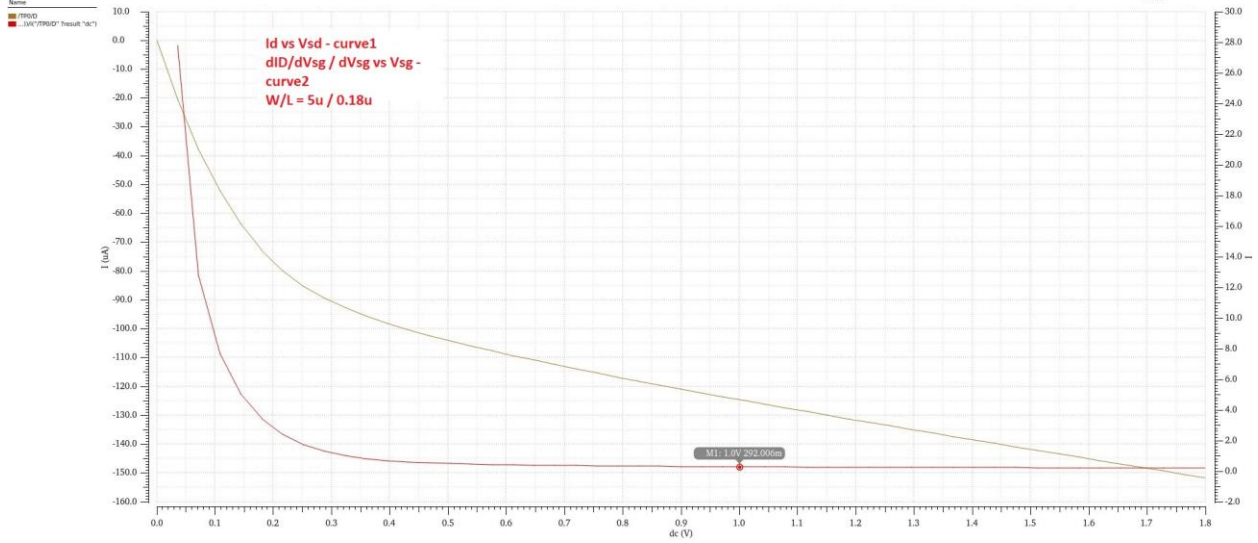


Circuit Used to Generate Frequency Response



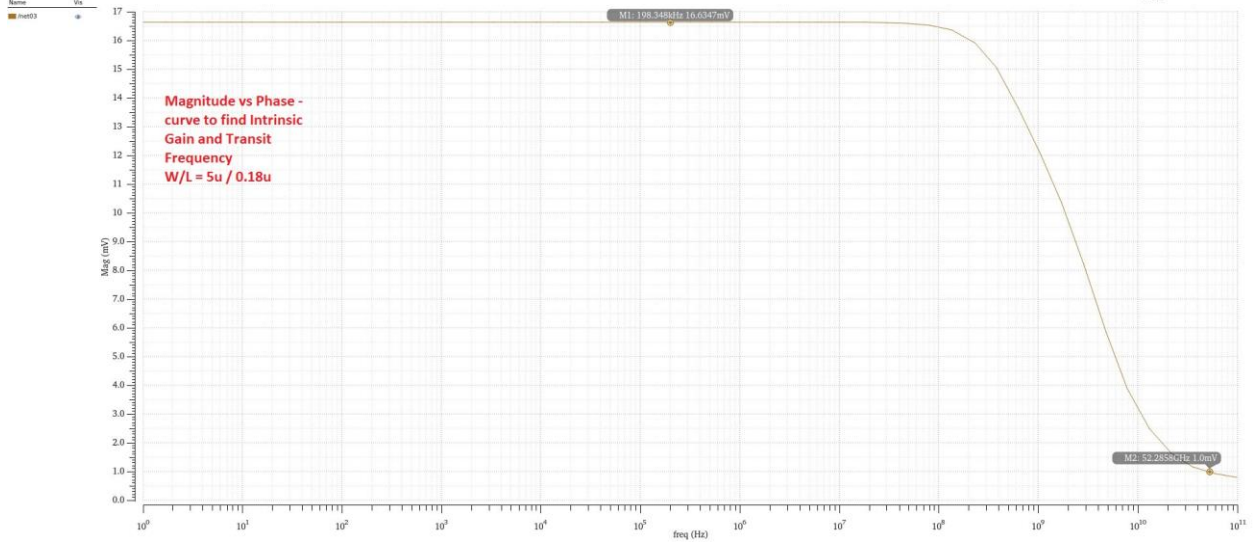
DC Response

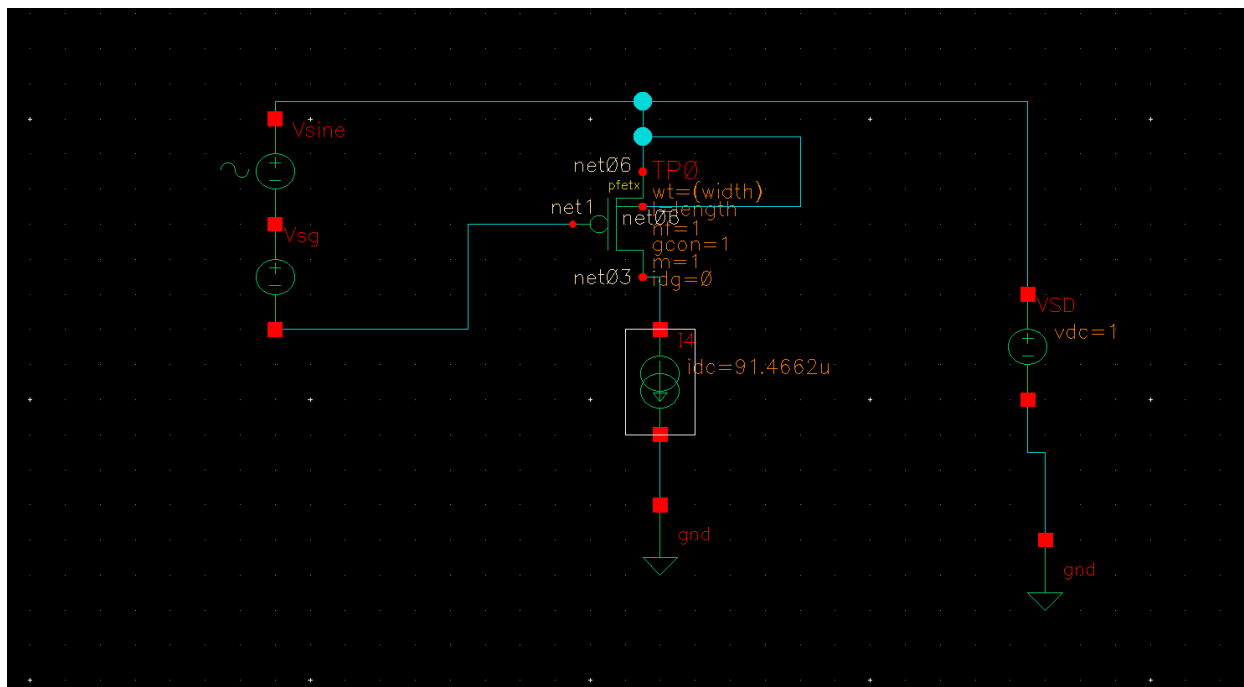
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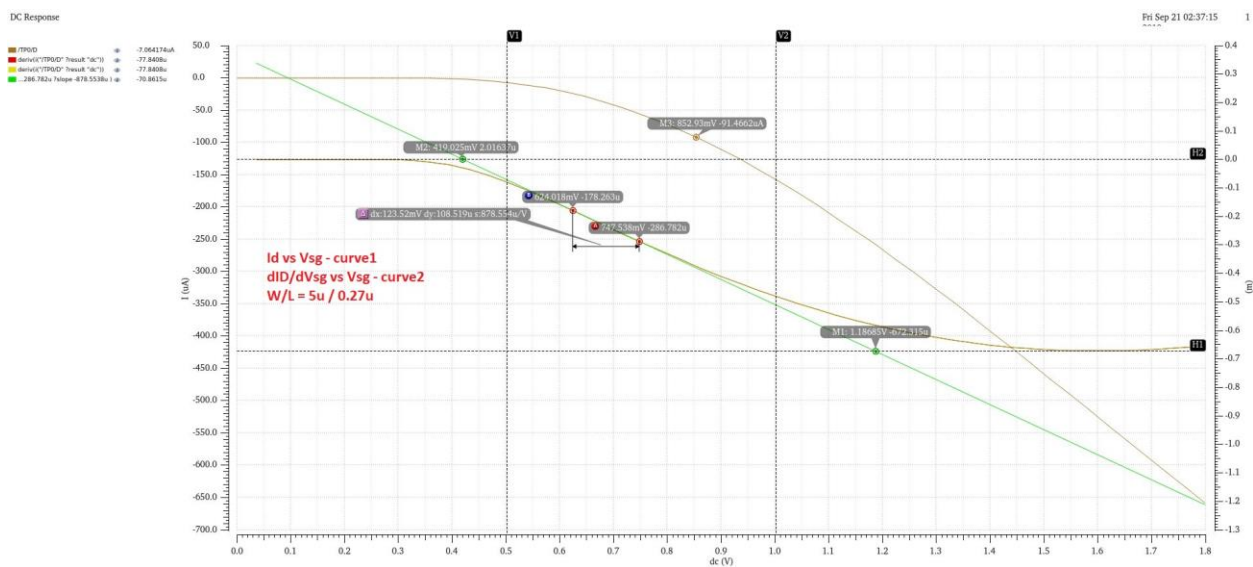
AC Response

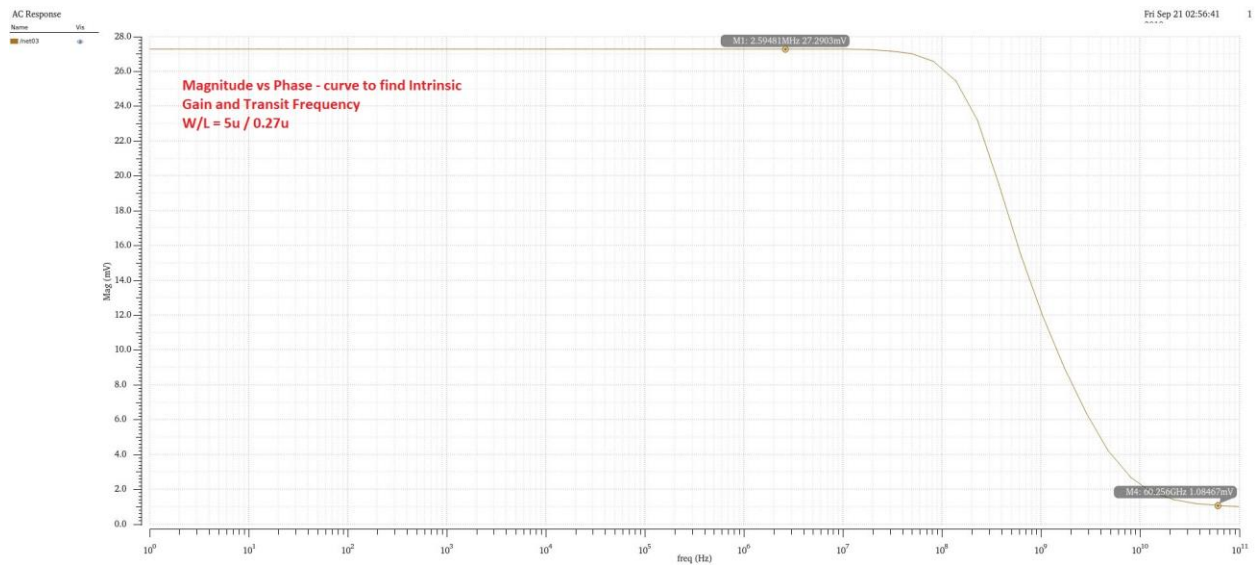
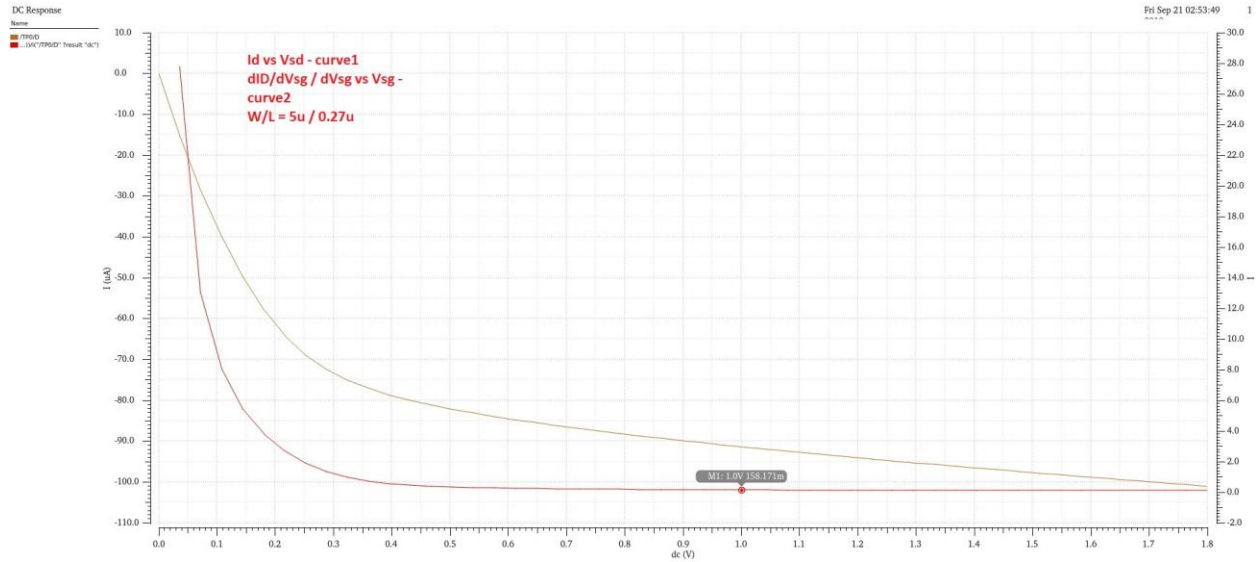
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Circuit Used to Generate Frequency Response





Result & Discussions

The parameter extraction for different MOS transistor was successfully done and the results are tabulated accordingly. The values include Biasing Voltage – Vgs , Biasing Current – Id , Vtn – Threshold Voltage , UnCox , Theta value , Lamda , Intrinsic Gain(Ai) , Unity Gain Frequency.

Type	W	L	Vgs (Volt)	Id (Amp)	Vtn (Volts)	UnCox	Theta	Lamba	Intrinsic Gain (Ai)	Unity Gain Frequency (Ft) (Hz)
nfetx	0.5u	0.18u	0.782756	28.0608u	459362	166.365u	0.91443	262.297m	21.16	53.663G
nfetx	5u	0.18u	0.70467	216.42u	458.321m	213.536u	1.27322	262m	21.6004	53.4717G
nfetx	5u	0.27u	0.74995	210.784u	442.657m	209.898	0.971645	224m	45.4602	51.1669G
pfetx	0.5u	0.18u	0.815354	-11.0077u	432.724	47.1424u	0.7515	289.478m	15.1356	54.0388G
pfetx	5u	0.18u	0.78846	-124.622u	413.066	55.91u	0.76815	292.006m	16.6347	52.2858G
pfetx	5u	0.27u	0.85293	-91.4662u	419.025	47.4419	0.65119	158.171m	27.2903	60.256G

Complete Tabulation of the results